

T-43-25

GEC PLESSEY
SEMICONDUCTORS

SL2363 & SL2364

VERY HIGH PERFORMANCE TRANSISTOR ARRAYS

The SL2363C and SL2364C are arrays of transistors internally connected to form a dual long-tailed pair with tail transistors. They are monolithic integrated circuits manufactured on a very high speed bipolar process which has a minimum useable fr of 2.5GHz, (typically 5GHz).

FEATURES

- Complete Dual Long-Tailed Pair in One Package
- Very High f_T – Typically 5 GHz
- Very Good Matching Including Thermal Matching

APPLICATIONS

- Wide Band Amplification Stages
- 140 and 560 MBit PCM Systems
- Fibre Optic Systems
- High Performance Instrumentation
- Radio and Satellite Communications

ORDERING INFORMATION

- SL2363 C CM
- SL2363 CB CM
- SL2364 C DC
- SL2364 C DP
- SL2364 C LC
- SL2364 C MP
- SL2364 CB DC

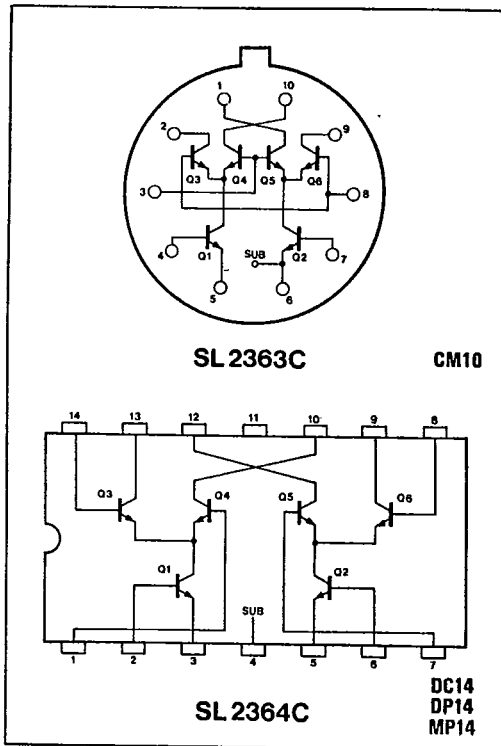


Fig. 1 Pin connections for CM, DC, DP and MP packages - top view. NOTE: See Fig. 4 for pinout of SL2364 in LC package

ELECTRICAL CHARACTERISTICS

Test conditions (unless otherwise stated):
 $T_{amb} = 22^{\circ}C \pm 2^{\circ}C$

| Characteristics | Value | | | Units | Conditions |
|------------------------------|-------|------|------|-----------------|---------------------------------|
| | Min. | Typ. | Max. | | |
| BVCBO | 10 | 20 | | V | $I_C = 10\mu A$ |
| LVCEO | 6 | 9 | | V | $I_C = 5mA$ |
| BVEBO | 2.5 | 5.0 | | V | $I_E = 10\mu A$ |
| BVCIO | 16 | 40 | | V | $I_C = 10\mu A$ |
| hFE | 50 | 80 | | | $I_C = 8mA, V_{CE} = 2V$ |
| f_T | 2.5 | 5 | | GHz | $I_C (Tail) = 8mA, V_{CE} = 2V$ |
| ΔV_{BE} (See note 1) | | 2 | 5 | mV | $I_C (Tail) = 8mA, V_{CE} = 2V$ |
| $\Delta V_{BE}/T_{AMB}$ | | -1.7 | | mV/ $^{\circ}C$ | $I_C (Tail) = 8mA, V_{CE} = 2V$ |
| CCB | | 0.5 | 0.8 | pF | $V_{CB} = 0$ |
| CCI | | 1.0 | 1.5 | pF | $V_{CI} = 0$ |

NOTE 1 ΔV_{BE} applies to $V_{BEQ3} - V_{BEQ4}$ and $V_{BEQ5} - V_{BEQ6}$

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TYPICAL CHARACTERISTICS

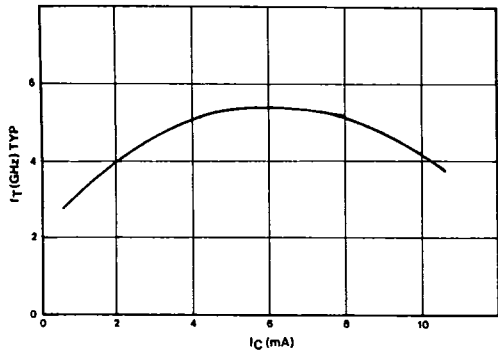


Fig. 2 Collector current

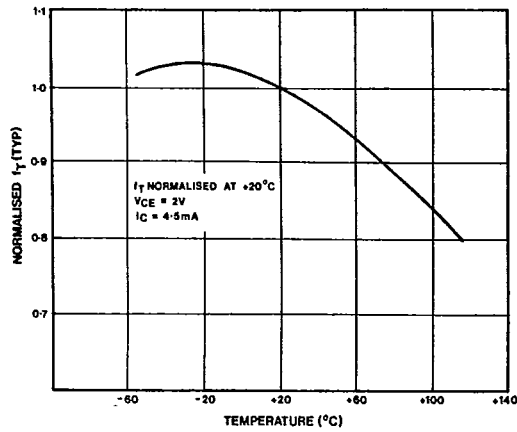


Fig. 3 Chip temperature

ABSOLUTE MAXIMUM RATINGS

Maximum individual transistor dissipation 200mW

Storage temperature $-55^{\circ}C$ to $+150^{\circ}C$

Maximum junction temperature $+150^{\circ}C$

Package thermal resistance ($^{\circ}C/W$):

Chip to case 85 (CM10)

Chip to ambient 225 (CM10) 175 (DP14)

$V_{CBO} = 10V$, $V_{EBO} = 2.5V$, $V_{CEO} = 6V$, $V_{C1O} = 15V$, I_C (any one transistor) = 20mA

The substrate should be connected to the most negative point of the circuit to maintain electrical isolation between the transistors.

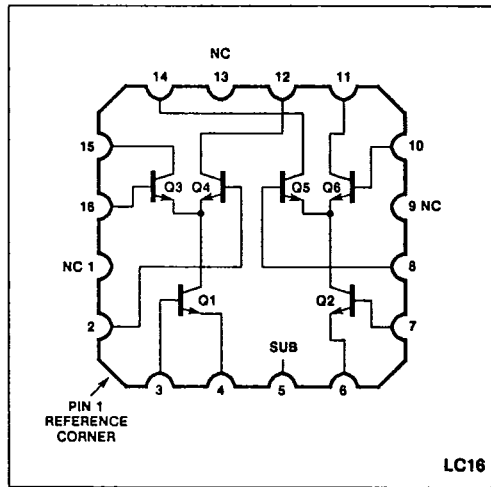


Fig.4 SL2364 LC pin connections